

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1	dio near luigi.in.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:03
2	BRS	L2	1147	438/710:ccls.	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:04
3	BRS	L3	12	2 and (hydrophobic)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:05

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	0	2 and (hydrophobic) near15 (pno-to-resist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:05
5	BRS	L5	1	2 and (hydrophobic) near15 (photo-resist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:06
6	BRS	L6	18	(hydrophobic) near15 (photo-resist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:13

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	1432	(hydrophobic) near15 (resist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:14
8	BRS	L8	89	(hydrophobic) near15 ((etch\$3 or remov\$3 or engrav\$3)) near10 (resist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:23
9	BRS	L9	4714	((etch\$3 or remov\$3 or engrav\$3)) near10 (photo-resist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:24

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	3354	((etch\$3)) near10 (photo-resist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:24
11	BRS	L11	2888	((remov\$3)) near10 (photo-resist)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:25
12	BRS	L12	2	((remov\$3)) near10 ((hydrophobic) near15 (photo-resist))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:25

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	539	((remov\$3)) near10 (photo-resist) near35 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 15:45
14	BRS	L14	663	((etch\$3)) near10 (photo-resist) near35 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:00
15	BRS	L15	1	((etch\$3)) near10 (photo-resist) near35 (barc) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:01

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	1	((etch\$3)) near10 (photo-resist) near35 (adhe\$3) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:01
17	BRS	L17	0	((remov\$3)) near10 (photo-resist) near35 (brac) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:02
18	BRS	L18	1	((remov\$3)) near10 (photo-resist) near35 (barc) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:02

	Type	L #	Hits	Search Text	DBs	Time Stamp
19	BRS	L19	5	((remov\$3)) near10 (photo-resist) near35 (adhe\$3) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:03
20	BRS	L20	0	((engrav\$3)) near10 (photo-resist) near35 (adhe\$3) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:03
21	BRS	L21	0	((engrav\$3)) near10 (photo-resist) near35 (barc\$3) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:03

	Type	L #	Hits	Search Text	DBs	Time Stamp
22	BRS	L22	0	((engrav\$3)) near10 (photo near resist) near35 (barc\$3) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:04
23	BRS	L23	0	((engrav\$3)) near10 (resist) near35 (barc\$3) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:04
24	BRS	L24	9	((remov\$3)) near10 (resist) near35 (barc\$3) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:07

	Type	L #	Hits	Search Text	DBs	Time Stamp
25	BRS	L25	212	((remov\$3)) near10 (resist) near35 (adhe\$3) near15 (substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:08
26	BRS	L26	21	((remov\$3)) near10 (resist) near35 (adhe\$3) near15 (etch\$3 near3 substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:19
27	BRS	L27	0	((engrav\$3)) near10 (resist) near35 (adhe\$3) near15 (etch\$3 near3 substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:12

	Type	L #	Hits	Search Text	DBs	Time Stamp
28	BRS	L28	59	(resist) near35 (adhe\$3) near15 (etch\$3 near3 substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:12
29	BRS	L29	1	(resist) near35 (adhe\$3) near15 (etch\$3 near3 substrate) near15 (acid)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:14
30	BRS	L30	0	(resist) near35 (barc\$3) near15 (etch\$3 near3 substrate) near15 (acid)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:14

	Type	L #	Hits	Search Text	DBs	Time Stamp
31	BRS	L31	6	(resist) near35 (barc\$3) near15 (etch\$3 near3 substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:15
32	BRS	L32	83	(resist) near35 (adher\$3) near15 (etch\$3 near3 substrate)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:15
33	BRS	L33	807	((remov\$3)) near10 (resist) near35 (adhe\$3)	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:19

	Type	L #	Hits	Search Text	DBs	Time Stamp
34	BRS	L34	854	((remov\$3)) near10 ((resist) near35 (adhe\$3))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:42
35	BRS	L35	78	((remov\$3)) near10 ((resist) near35 (barc))	US- PGPUB ; USPAT ; EPO; JPO; DERWE NT; IBM_T DB	2005/01/1 7 16:42

	U	1	Document ID	Title	Current OR
1			US 20040152329 A1	Method for manufacturing semiconductor electronic devices	438/710
2			US 20040050406 A1	Compositions and method for removing photoresist and/or resist residue at pressures ranging from ambient to supercritical	134/26
3			US 20040029307 A1	Method for manufacturing electronic circuits integrated on a semiconductor substrate	438/48
4			US 20040011386 A1	Composition and method for removing photoresist and/or resist residue using supercritical fluids	134/26
5			US 20040002214 A1	Method of manufacturing trench structure for device	438/689

	U	1	Document ID	Title	Current OR
6			US 20030077523 A1	Method of manufacturing a mask blank and a mask, the mask blank and the mask, and useless film removing method and apparatus	430/5
7			US 20020171818 A1	Optical exposure method, device manufacturing method and lithographic projection apparatus	355/69
8			US 6618118 B2	Optical exposure method, device manufacturing method and lithographic projection apparatus	355/30
9			US 6121123 A	Formation of gate on semiconductor substrate consists of using thin film as both a bottom anti-reflective coating and a hard mask to control the critical dimension of the gate	